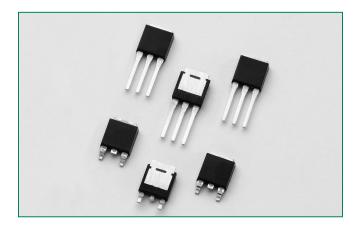


# LJxx06xx & QJxx06xHx series

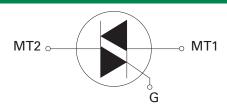




#### **Main Features**

Symbol	Value	Unit
I <sub>T(RMS)</sub>	6	А
V <sub>DRM</sub> /V <sub>RRM</sub>	400 or 600	V
I <sub>GT (Q1)</sub>	10 to 35	mA

#### **Schematic Symbol**



# **PRELIMINARY & CONFIDENTIAL**

Littelfuse, Inc. has characterized initial samples of this device and is currently conducting reliability testing. Parts numbers and specifications are subject to change until the datasheet is made final.

#### **Description**

This 6 A High Temperature Alternistor Triac solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Sensitive type components guarantee gate control in Quadrants I & IV needed for digital control circuitry.

Alternistor type components only operate in quadrants I, II, & III and are used in circuits requiring high dv/dt capability.

#### **Features & Benefits**

- RoHS compliant
- 150°C maximum junction temperature
- Voltage capability up to 600V
- Surge capability up to 72A at 60Hz half cycle
- Solid-state switching eliminates arcing or contact bounce that create voltage transients
- No contacts to wear out from reaction of switching events
- Restricted (or limited) RFI generation, depending on activation point of sine wave
- Requires only a small gate activation pulse in each half-cycle
- Halogen free and RoHS compliant

# **Applications**

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, light dimmers, power tools, home/brown goods and white goods appliances.

Alternistor Triacs (no snubber required) are used in applications with high inductive loads requiring the highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

# Absolute Maximum Ratings — Sensitive Triac (4 Quadrants)

Symbol	Par	Value	Unit		
$V_{\rm DSM}/V_{\rm RSM}$	Peak non-repetitive blocking voltage	Pw=100 μs		700	V
I <sub>T(RMS)</sub>	RMS on-state current (full sine wave)	LJxx06Vy/LJxx06Dy	T <sub>c</sub> = 125°C	6	А
1	Non repetitive surge peak on-state current	f = 50 Hz	t = 20 ms	60	А
TSM	(full cycle, T <sub>J</sub> initial = 25°C)	f = 60 Hz	t = 16.7 ms	72	1 ^
l²t	I²t Value for fusing	$t_{p} = 8.3 \text{ ms}$	21.5	A <sup>2</sup> s	
di/dt	Critical rate of rise of on-state current $I_{G} = 50$ mA with 0.1 $\mu$ s rise time	f = 60 Hz	T <sub>J</sub> = 150°C	70	A/µs
I <sub>GTM</sub>	Peak gate trigger current	t <sub>p</sub> ≤ 10 μs	T <sub>J</sub> = 150°C	1.6	А
P <sub>G(AV)</sub>	Average gate power dissipation	0.4	W		
T <sub>stg</sub>	Storage temperature range	-40 to 150	°C		
T,	Operating junction temperature range	-40 to 150	°C		

Note: xx=voltage/10, y = sensitivity



# **Thyristors** 6 Amp High Temp Sensitive & Alternistor (High Co Little 1946) 2016 1993 Characterized High Samp

# Absolute Maximum Ratings — Alternistor Triac (3 Quadrants)

Symbol	Pa	Value	Unit			
$V_{\rm DSM}/V_{\rm RSM}$	Peak non-repetitive blocking voltage		Pw=100 µ	IS	700	V
I <sub>T(RMS)</sub>	RMS on-state current (full sine wave)	QJxx06VHy/	QJxx06DHy	T <sub>c</sub> = 130°C	6	А
	Non repetitive surge peak on-state current		t = 20 ms	QJxx06VHy QJxx06DHy	60	А
I <sub>TSM</sub>		f = 60 Hz	t = 16.7 ms	QJxx06VHy QJxx06DHy	72	A
l²t	I²t Value for fusing	$t_{p} = 8.$	3 ms	QJxx06VHy QJxx06DHy	21.5	A²s
di/dt	Critical rate of rise of on-state current	f = 6	) Hz	T <sub>J</sub> = 150°C	70	A/µs
I <sub>GTM</sub>	Peak gate trigger current	t <sub>p</sub> ≤ 10 μs;	$I_{\text{GT}} \leq I_{\text{GTM}}$	T <sub>J</sub> = 150°C	1.2	А
P <sub>G(AV)</sub>	Average gate power dissipation			T <sub>J</sub> = 150°C	0.3	W
T <sub>stg</sub>	Storage temperature range				-40 to 150	°C
T <sub>J</sub>	Operating junction temperature range				-40 to 150	°C

Note: xx=voltage/10, y = sensitivity

# Electrical Characteristics (T<sub>J</sub> = 25°C, unless otherwise specified) — Sensitive Triac (4 Quadrants)

Symbol	Test Conditions	Quadrant		Value LJxx06x8	Unit	
I <sub>GT</sub>	$V_{D} = 12V R_{1} = 60 \Omega$	I – II – III IV	MAX.	10 20	mA	
V <sub>GT</sub>	, , , , , , , , , , , , , , , , , , ,	ALL	MAX.	1.2	V	
V <sub>GD</sub>	$V_D = V_{DRM} R_L = 3.3 \text{ k}\Omega T_J = 150 ^{\circ}\text{C}$	ALL	MIN.	0.15	V	
I <sub>H</sub>	I <sub>T</sub> = 100mA		MAX.	25	mA	
dv/dt	V - V Cata Open T - 150°C	400V	TYP.	80	V/µs	
αν/αι	$V/dt$ $V_D = V_{DRM}$ Gate Open $T_J = 150$ °C		116.	50	v/μs	
(dv/dt)c	$(di/dt)c = 3.2 \text{ A/ms } T_J = 150^{\circ}\text{C}$		TYP.	2	V/µs	
t <sub>gt</sub>	$I_{G} = 2 \times I_{GT} \text{ PW} = 15 \mu \text{s} I_{T} = 8.5 \text{ A(pk)}$		TYP.	12	μs	

Note: xx=voltage/10, x = package

# Electrical Characteristics (T<sub>J</sub> = 25°C, unless otherwise specified) — Alternistor Triac (3 Quadrants)

Cumbal	Symbol Test Conditions		Quadrant		Va	Unit	
Symbol			Quadrant			QJxx06xH4	Onit
I <sub>GT</sub>	V - 12V P - 60 O	1 – 11 – 111	MAX.		10	35	mA
V <sub>GT</sub>	$V_D = 12V R_L = 60 \Omega$	1 – 11 – 111	MAX.		1.	3	V
$V_{\rm GD}$	$V_D = V_{DRM} R_L = 3.3 \text{ k}\Omega T_J = 150^{\circ}\text{C}$ $I - II - III$		MIN.		0.15		V
I <sub>H</sub>	$I_{T} = 100 \text{mA}$		MAX.		25	35	mA
alv (/al+	V V Cata Open T 150°C	QJxx06VHY/	NAINI	400V	150	350	\//
av/at	$dv/dt$ $V_D = V_{DRM}$ Gate Open $T_J = 150$ °C	QJxx06DHy MIN.	IVIIIN.	600V	100	250	V/µs
(dv/dt)c	$(di/dt)c = 3.2 \text{ A/ms T}_J = 150^{\circ}\text{C}$		MIN.		15	20	V/µs
t <sub>gt</sub>	$I_{G} = 2 \times I_{GT} \text{ PW} = 15 \mu \text{s} I_{T} = 8.5 \text{ A(pk)}$		TYP.		10	10	μs

Note: xx=voltage/10, x = package

# **Thyristors**

# 6 Amp High Temp Sensitive & Alternistor (High Commutation) Triacs

### **Static Characteristics**

Symbol	Test Conditions					Value	Unit
$V_{TM}$		I <sub>TM</sub> = 8.4 A	t <sub>p</sub> = 380 μs		MAX.	1.40	V
		$T_{_{\rm J}}=25^{\circ}{\rm C}$	400 - 600V		10	μΑ	
		LJxx06xy	T <sub>J</sub> = 125°C	400 - 600V	MAX.	0.5	- mA
1 /1	., .,		T <sub>J</sub> = 150°C	400 - 600V		3	
I <sub>DRM</sub> / I <sub>RRM</sub>	$I_{DRM} / I_{RRM}$ $V_{DRM} = V_{RRM}$	$V_{DRM} = V_{RRM}$ $QJxx06xHy$	T <sub>J</sub> = 25°C	400 - 600V		10	μA
			T <sub>J</sub> = 125°C	400 - 600V		0.5	A
			T <sub>J</sub> = 150°C	400 - 600V		3	mA

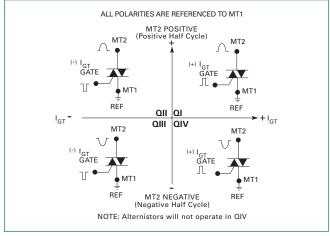
Note: xx=voltage/10, x = package, y = sensitivity

# **Thermal Resistances**

Symbol	Parameter		Value	Unit
$R_{\theta(JC)}$	Junction to case (AC)	LJ/QJxx06Vyy LJ/QJxx06Dyy	1.3	°C/W
$R_{\scriptscriptstyle{\theta(J-A)}}$	Junction to ambient	LJ/QJxx06Vyy LJ/QJxx06Dyy	70	°C/W

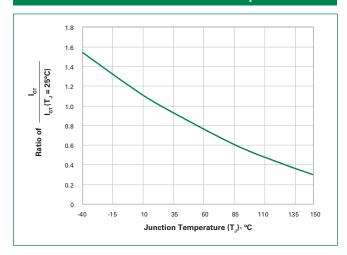
Note: xx=voltage/10, y = sensitivity

**Figure 1: Definition of Quadrants** 



Note: Alternistors will not operate in QIV

Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature



#### **PRELIMINARY & CONFIDENTIAL**

Littelfuse, Inc. has characterized initial samples of this device and is currently conducting reliability testing. Parts numbers and specifications are subject to change until the datasheet is made final.



Figure 3: Normalized DC Holding Current vs. Junction Temperature

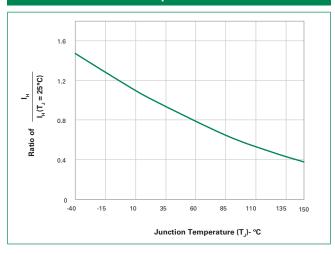


Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature

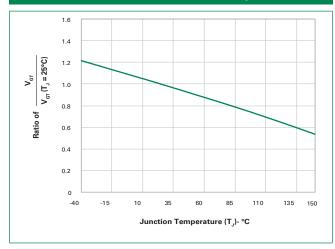


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

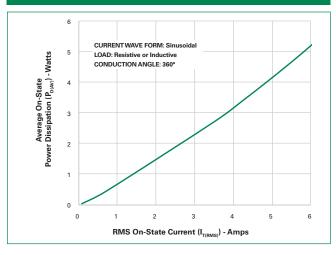


Figure 6: Maximum Allowable Case Temperature vs. On-State Current

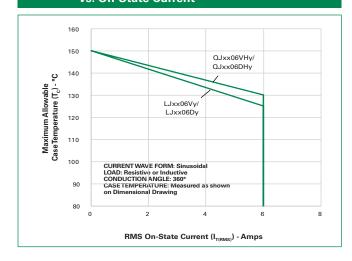
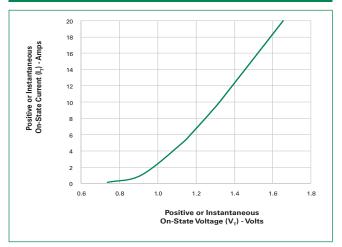


Figure 7: On-State Current vs. On-State Voltage (Typical)

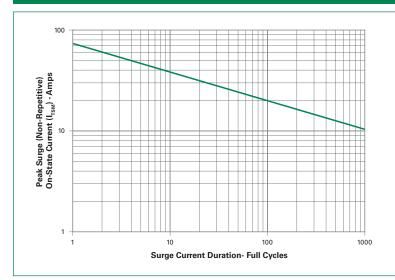


#### PRELIMINARY & CONFIDENTIAL

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### Figure 8: Surge Peak On-State Current vs. Number of Cycles



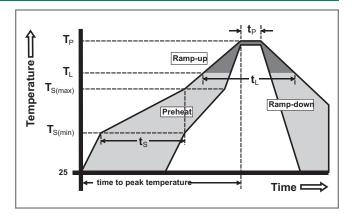
SUPPLY FREQUENCY: 60 Hz Sinusoidal LOAD: Resistive RMS On-State Current: [I<sub>T(RMS)</sub>I: Maximum Rated Value at Specified Case Temperature

#### Notes:

- Gate control may be lost during and immediately following surge current interval.
- Overload may not be repeated until junction temperature has returned to steady-state rated value.

#### **Soldering Parameters**

Reflow Co	ndition	Pb – Free assembly	
	-Temperature Min (T <sub>s(min)</sub> )	150°C	
Pre Heat	-Temperature Max (T <sub>s(max)</sub> )	200°C	
	-Time (min to max) (t <sub>s</sub> )	60 – 180 secs	
Average ra	amp up rate (LiquidusTemp) k	5°C/second max	
T <sub>S(max)</sub> to T <sub>L</sub>	- Ramp-up Rate	5°C/second max	
Reflow	-Temperature (T <sub>L</sub> ) (Liquidus)	217°C	
nellow	-Time (t <sub>L</sub> )	60 – 150 seconds	
PeakTemp	erature (T <sub>P</sub> )	260 <sup>+0/-5</sup> °C	
Time with Temperatu	in 5°C of actual peak ıre (t <sub>p</sub> )	20 – 40 seconds	
Ramp-dov	vn Rate	5°C/second max	
Time 25°C	to peakTemperature (T <sub>P</sub> )	8 minutes Max.	
Do not exc	ceed	280°C	



### **PRELIMINARY & CONFIDENTIAL**

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# **Physical Specifications**

Terminal Finish 100% Matte Tin-plated			
Body Material	UL recognized compound meeting flammability rating V-0.		
Terminal Material	Copper Alloy		

# **Design Considerations**

Careful selection of the correct component for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

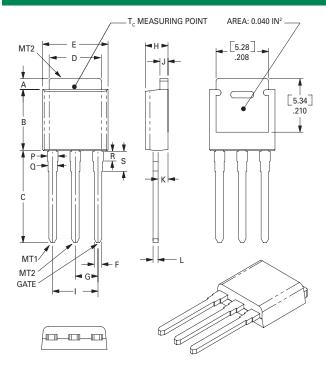
### **Environmental Specifications**

Test	Specifications and Conditions
AC Blocking (V <sub>DRM</sub> )	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 150°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -55°C to +150°C; 15-min dwell-time
Temperature/ Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 160V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

#### PRELIMINARY & CONFIDENTIAL

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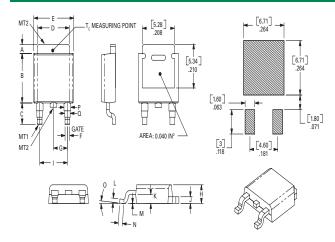
# Dimensions — TO-251AA (V-Package) — V-PAK Through Hole



Dimension		Inches		IV.	1illimete:	rs
Difficusion	Min	Тур	Max	Min	Тур	Max
А	0.037	0.040	0.043	0.94	1.01	1.09
В	0.235	0.242	0.245	5.97	6.15	6.22
С	0.350	0.361	0.375	8.89	9.18	9.53
D	0.205	0.208	0.213	5.21	5.29	5.41
Е	0.255	0.262	0.265	6.48	6.66	6.73
F	0.027	0.031	0.033	0.69	0.80	0.84
G	0.087	0.090	0.093	2.21	2.28	2.36
Н	0.085	0.092	0.095	2.16	2.34	2.41
I	0.176	0.180	0.184	4.47	4.57	4.67
J	0.018	0.020	0.023	0.46	0.51	0.58
K	0.035	0.037	0.039	0.90	0.95	1.00
L	0.018	0.020	0.023	0.46	0.52	0.58
Р	0.042	0.047	0.052	1.06	1.20	1.32
Q	0.034	0.039	0.044	0.86	1.00	1.11
R	0.034	0.039	0.044	0.86	1.00	1.11
S	0.074	0.079	0.084	1.86	2.00	2.11



# Dimensions - TO-252AA (D-Package) - D-PAK Surface mount



#### Dimension Max Тур Тур Α 0.037 0.040 0.043 0.94 1.01 1.09 В 0.235 5.97 6.22 0.243 0.245 6.16 С 0.106 0.108 0.113 2.69 2.74 2.87 D 0.205 0.208 0.213 5.21 5.29 5.41 Ε 0.255 0.262 0.265 6.48 6.65 6.73 F 0.027 0.031 0.033 0.69 0.80 0.84 G 0.087 0.090 0.093 2.21 2.28 2.36 Н 0.085 0.092 0.095 2.16 2.33 2.41 0.176 0.179 0.184 4.47 4.55 4.67 J 0.018 0.020 0.023 0.46 0.51 0.58 Κ 0.035 0.037 0.039 0.90 0.95 1.00 L 0.018 0.020 0.023 0.46 0.51 0.58 Μ 0.000 0.000 0.004 0.00 0.00 0.10 Ν 0.021 0.026 0.027 0.53 0.67 0.69 0 0° 0° 5° 0° 0° 5° Ρ 0.042 0.047 0.052 1.06 1.20 1.32 Q 0.034 0.039 0.044 0.86 1.00 1.11

Inches

#### PRELIMINARY & CONFIDENTIAL

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### **Product Selector**

Deat November	Vol	tage	Gate Sensitiv	rity Quadrants	T	Dooleana	
Part Number	400V	600V	1 - 11 - 111	IV	Туре	Package	
LJxx06D8	Х	Х	10	20	Sensitive Triac	TO-252 D-PAK	
LJxx06V8	Х	×	10	20	Sensitive Triac	TO-251 V-PAK	
QJxx06DH3	Х	×	10		Alternistor Triac	TO-252 D-PAK	
QJxx06VH3	Х	×	10		Alternistor Triac	TO-251 V-PAK	
QJxx06DH4	Х	×	35		Alternistor Triac	TO-252 D-PAK	
QJxx06VH4	Х	х	35		Alternistor Triac	TO-251 V-PAK	

Note: xx = voltage/10

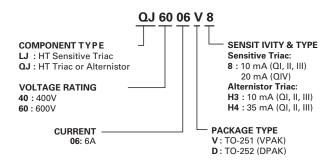
# **Packing Options**

Part Number	Marking	Weight	Packing Mode	Base Quantity
LJxx06D8TP	LJxx06D8	0.3g	Tube Pack	750(75 per tube)
LJxx06D8RP	LJxx06D8	0.3g	Embossed Carrier	2500
LJxx06V8TP	LJxx06V8	0.4g	Tube Pack	750(75 per tube)
QJxx06DH3TP	QJxx06DH3	0.3g	Tube Pack	750(75 per tube)
QJxx06DH3RP	QJxx06DH3	0.3g	Embossed Carrier	2500
QJxx06VH3TP	QJxx06VH3	0.4g	Tube Pack	750(75 per tube)
QJxx06DH4TP	QJxx06DH4	0.3g	Tube Pack	750(75 per tube)
QJxx06DH4RP	QJxx06DH4	0.3g	Embossed Carrier	2500
QJxx06VH4TP	QJxx06VH4	0.4g	Tube Pack	750(75 per tube)

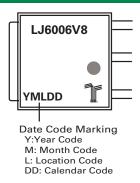
Note: xx = voltage/10



### **Part Numbering System**

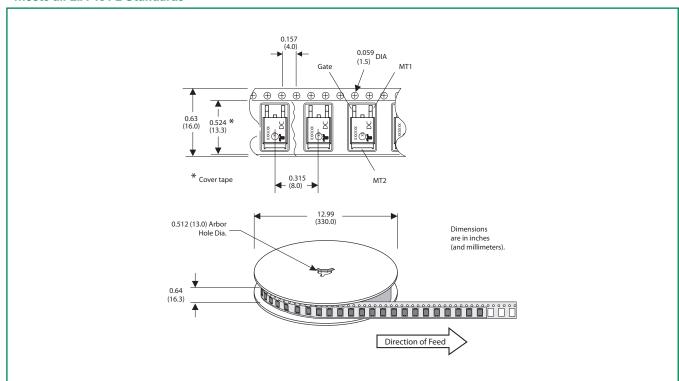


# **Part Marking System**



#### TO-252 Embossed Carrier Reel Pack (RP) Specifications

#### Meets all EIA-481-2 Standards



# PRELIMINARY & CONFIDENTIA

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